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TABLE OF CONTENTS

FUTURE LOGIC SCALING: TOWARDS ATOMIC CHANNELS AND DECONSTRUCTED CHIPS	1
<i>S. B. Samavedam; J. Ryckaert; E. Beyne; K. Ronse; N. Horiguchi; Z. Toket; I. Radu; M. G. Bardon; M. H. Na; A. Spessot; S. Biesemans</i>	
TOWARD HIGH-PERFORMANCE AND RELIABLE GE CHANNEL DEVICES FOR 2 NM NODE AND BEYOND	11
<i>H. Arimura; E. Capogreco; A. Vohra; C. Porret; R. Loo; E. Rosseel; A. Hikavy; D. Cott; G. Boccardi; L. Witters; G. Eneman; J. Mitard; N. Collaert; N. Horiguchi</i>	
GATE-ALL-AROUND STRAINED $Si_{0.4}Ge_{0.6}$ NANOSHEET PMOS ON STRAIN RELAXED BUFFER FOR HIGH PERFORMANCE LOW POWER LOGIC APPLICATION	15
<i>A. Agrawal; S. Chouksey; W. Rachmady; S. Vishwanath; S. Ghose; M. Mehta; J. Torres; A. A. Oni; X. Weng; H. Li; D. Merrill; M. Metz; A. Murthy; J. Kavalieros</i>	
STACKED GATE-ALL-AROUND NANOSHEET PFET WITH HIGHLY COMPRESSIVE STRAINED $Si_{1-x}Ge_x$ CHANNEL	19
<i>S. Mochizuki; M. Bhuiyan; H. Zhou; J. Zhang; E. Stuckert; J. Li; K. Zhao; M. Wang; V. Basker; N. Loubet; D. Guo; B. Haran; H. Bu</i>	
FIRST DEMONSTRATION OF UNIFORM 4-STACKED $Ge_{0.9}Sn_{0.1}$ NANOSHEETS WITH RECORD ION $=73\mu A$ AT $V_{OV}=V_{DS}=-0.5V$ AND LOW NOISE USING DOUBLE $Ge_{0.95}Sn_{0.05}$ CAPS, DRY ETCH, LOW CHANNEL DOPING, AND HIGH S/D DOPING	23
<i>Yu-Shiang Huang; Chung-En Tsai; Chien-Te Tu; Jyun-Yan Chen; Hung-Yu Ye; Fang-Liang Lu; C. W. Liu</i>	
SUBBAND ENGINEERING BY COMBINATION OF CHANNEL THICKNESS SCALING AND (111) SURFACE ORIENTATION IN INAS-ON-INSULATOR NMOSFETS	27
<i>K. Sumita; K. Toprasertpong; M. Takenaka; S. Takagi</i>	
SOURCES OF VARIABILITY IN SCALED MOS_2 FETS	31
<i>Quentin Smets; Devin Verreck; Yuanyuan Shi; Goutham Arutchevan; Benjamin Groven; Xiangyu Wu; Surajit Sutar; Sreetama Banerjee; Ankit Nalin Mehta; Dennis Lin; Inge Asselberghs; Iuliana Radu</i>	
RELIABILITY OF ULTRATHIN HIGH-κ DIELECTRICS ON CHEMICAL-VAPOR DEPOSITED 2D SEMICONDUCTORS	35
<i>Zhihao Yu; Hongkai Ning; Chao-Ching Cheng; Weisheng Li; Lei Liu; Wanqing Meng; Zhongzhong Luo; Taotao Li; Songhua Cai; Peng Wang; Wen-Hao Chang; Chao-Hsin Chien; Yi Shi; Yong Xu; Lain-Jong Li; Xinran Wang</i>	
PINNING-FREE EDGE CONTACT MONOLAYER MOS_2 FET	39
<i>Terry Y. T. Hung; Shih-Yun Wang; Chih-Piao Chuu; Yun-Yan Chung; Ang-Sheng Chou; Feng-Shew Huang; Tac Chen; Ming-Yang Li; Chao-Ching Cheng; Jin Cai; Chao-Hsin Chien; Wen-Hao Chang; H.-S. Philip Wong; Lain-Jong Li</i>	
SUB-1NM EOT WS_2-FET WITH $I_{DS} > 600\mu A/\mu M$ AT $V_{DS}=1V$ AND $SS < 70MV/DEC$ AT $L_G=40NM$	43
<i>Chin-Sheng Pang; Peng Wu; Joerg Appenzeller; Zhihong Chen</i>	
SUB-0.5 NM INTERFACIAL DIELECTRIC ENABLES SUPERIOR ELECTROSTATICS: 65 MV/DEC TOP-GATED CARBON NANOTUBE FETS AT 15 NM GATE LENGTH	47
<i>G. Pitner; Z. Zhang; Q. Lin; S.-K. Su; C. Gilardi; C. Kuo; H. Kashyap; T. Weiss; Z. Yu; T. -A. Chao; L.-J. Li; S. Mitra; H.-S. P. Wong; J. Cai; A. Kummel; P. Bandaru; M. Passlack</i>	
DUAL GATE SYNTHETIC WS_2 MOSFETS WITH $120\mu S/\mu M$ GM $2.7\mu F/CM^2$ CAPACITANCE AND AMBIPOLAR CHANNEL	51
<i>Dennis Lin; Xiangyu Wu; Daire Cott; Devin Verreck; Benjamin Groven; Stephanie Sergeant; Quentin Smets; Surajit Sutar; Inge Asselberghs; Iuliana Radu</i>	
MULTISCALE SIMULATION OF FERROELECTRIC TUNNEL JUNCTION MEMORY ENABLED BY VAN DER WAALS HETEROJUNCTION: COMPARISON TO EXPERIMENT AND PERFORMANCE PROJECTION	55
<i>Ning Yang; Hung-Yu Chen; Jiangbin Wu; Tong Wu; Jun Cao; X. Ling; H. Wang; J. Guo</i>	
FERROELECTRIC SWITCHING IN FEFET: PHYSICS OF THE ATOMIC MECHANISM AND SWITCHING DYNAMICS IN $HfZrO_x$, HfO_2 WITH OXYGEN VACANCIES AND SI DOPANTS	59
<i>Sergiu Clima; B. J. O'Sullivan; N. Ronchi; M. G. Bardon; K. Banerjee; G. Van Den Bosch; G. Pourtois; J. Van Houdt</i>	
FERROELECTRIC THICKNESS DEPENDENT DOMAIN INTERACTIONS IN FEFETS FOR MEMORY AND LOGIC: A PHASE-FIELD MODEL BASED ANALYSIS	63
<i>A. K. Saha; M. Si; K. Ni; S. Datta; P. D. Ye; S. K. Gupta</i>	
EXAMINATION OF THE INTERPLAY BETWEEN POLARIZATION SWITCHING AND CHARGE TRAPPING IN FERROELECTRIC FET	67
<i>Shan Deng; Zhouhang Jiang; Sourav Dutta; Huacheng Ye; Wriddhi Chakraborty; Santosh Kurinec; Suman Datta; Kai Ni</i>	
DEPOLARIZATION FIELD INDUCED INSTABILITY OF POLARIZATION STATES IN HfO_2 BASED FERROELECTRIC FET	71
<i>Zheng Wang; Muhammad Mainul Islam; Panni Wang; Shan Deng; Shimeng Yu; Asif Islam Khan; Kai Ni</i>	
BEOL-COMPATIBLE MULTIPLE METAL-FERROELECTRIC-METAL (M-MFM) FETS DESIGNED FOR LOW VOLTAGE (2.5 V), HIGH DENSITY, AND EXCELLENT RELIABILITY	75
<i>Meng-Hui Yan; Ming-Hung Wu; Hsin-Hui Huang; Yu-Hao Chen; Yueh-Hua Chu; Tian-Li Wu; Po-Chun Yeh; Chih-Yao Wang; Yu-De Lin; Jian-Wei Su; Pei-Jer Tzeng; Shyh-Shyuan Sheu; Wei-Chung Lo; Chih-I Wu; Tuo-Hung Hou</i>	

DEVELOPMENT OF HIGH-VOLTAGE VERTICAL GAN PN DIODES	79
<i>R. J. Kaplar; B. P. Gunning; A. A. Allerman; M. H. Crawford; J. D. Flicker; A. M. Armstrong; L. Yates; A. T. Binder; J. R. Dickerson; G. Pickrell; P. Sharps; T. Anderson; J. Gallagher; A. Jacobs; A. Koehler; M. Tadjer; K. Hobart; M. Ebrish; M. Porter; R.</i>	
DEMONSTRATION OF A ~40 KV SI VACUUM TRANSISTOR AS A PRACTICAL HIGH FREQUENCY AND POWER DEVICE	83
<i>W. Chern; G. Rughoobur; A. Zubair; N. Karaulac; A. Cramer; R. Gupta; T. Palacios; A. Akinwande</i>	
3.3 KV BACK-GATE-CONTROLLED IGBT (BC-IGBT) USING MANUFACTURABLE DOUBLE-SIDE PROCESS TECHNOLOGY	87
<i>T. Saraya; K. Itou; T. Takakura; M. Fukui; S. Suzuki; K. Takeuchi; M. Tsukuda; K. Satoh; T. Matsudai; K. Kakushima; T. Hoshii; K. Tsutsui; H. Iwai; A. Ogura; W. Saito; S. Nishizawa; I. Omura; H. Ohashi; T. Hiramoto</i>	
5 KV MULTI-CHANNEL ALGAN/GAN POWER SCHOTTKY BARRIER DIODES WITH JUNCTION-FIN-ANODE	91
<i>M. Xiao; Y. Ma; Z. Du; X. Yan; R. Zhang; K. Cheng; K. Liu; A. Xie; E. Beam; Y. Cao; H. Wang; Y. Zhang</i>	
FIELD-INDUCED ACCEPTOR IONIZATION IN ENHANCEMENT-MODE GAN P-MOSFETS	95
<i>Nadim Chowdhury; Qingyun Xie; John Niroula; Nitul S. Rajput; Kai Cheng; Han Wui Then; Tomás Palacios</i>	
DIAMOND SEMICONDUCTOR DEVICES, STATE-OF-THE-ART OF MATERIAL GROWTH AND DEVICE PROCESSING	99
<i>H. Umezawa</i>	
PAST AND FUTURE OF 3D FLASH	103
<i>Johann Alsmeyer; Masaaki Higashitani; Sunhom Steve Paak; Siva Sivaram</i>	
CAPACITANCE BOOSTING BY ANTI-FERROELECTRIC BLOCKING LAYER IN CHARGE TRAP FLASH MEMORY DEVICE	107
<i>Eui Joong Shin; Sung Won Shin; Seung Hwan Lee; Tae In Lee; Min Ju Kim; Hyun Jun Ahn; Jae Hwan Kim; Wan Sik Hwang; Jaeduk Lee; Byung Jin Cho</i>	
A VERTICAL SPLIT-GATE FLASH MEMORY FEATURING HIGH-SPEED SOURCE-SIDE INJECTION PROGRAMMING, READ DISTURB FREE, AND 100K ENDURANCE FOR EMBEDDED FLASH (EFLASH) SCALING AND COMPUTING-IN-MEMORY (CIM)	111
<i>Tzu-Hsuan Hsu; Hang-Ting Lue; Po-Kai Hsu; Teng-Hao Yeh; Pei-Ying Du; Guan-Ru Lee; Chia-Jung Chiu; Keh-Chung Wang; Chih-Yuan Lu</i>	
3D AND: A 3D STACKABLE FLASH MEMORY ARCHITECTURE TO REALIZE HIGH-DENSITY AND FAST-READ 3D NOR FLASH AND STORAGE-CLASS MEMORY	115
<i>Hang-Ting Lue; Guan-Ru Lee; Teng-Hao Yeh; Tzu-Hsuan Hsu; Chieh Roger Lo; Cheng-Lin Sung; Wei-Chen Chen; Chia-Tze Huang; Kuan-Yuan Shen; Meng-Yen Wu; Pishan Tseng; Min-Feng Hung; Chia-Jung Chiu; Kuang-Yeu Hsieh; Keh-Chung Wang; Chih-Yuan Lu</i>	
INDUSTRY'S FIRST RECESSED GATE TRANSISTOR TECHNOLOGY FOR SENSE AMPLIFIER CIRCUIT IN DRAM: PHENOMENA OF RANDOMLY THRESHOLD VOLTAGE HIGH FLYING AND SUBTHRESHOLD SWING DEGRADATION	119
<i>Dongyeon Oh; Heejung Yang; Seonyong Cha; Seungchul Lee; Sungkye Park; Jinkook Kim</i>	
A STACKED EMBEDDED DRAM ARRAY FOR LPDDR4/4X USING HYBRID BONDING 3D INTEGRATION WITH 34GB/S/1GB 0.88PJ/B LOGIC-TO-MEMORY INTERFACE	123
<i>Bai Fujun; Jiang Xiping; Wang Song; Yu Bing; Tan Jie; Zuo Fengguo; Wang Chunjuan; Wang Fan; Long Xiaodong; Yu Guoqing; Fu Ni; Li Qiannan; Li Hua; Wang Kexin; Duan Huifu; Bai Liang; Jia Xuerong; Li Jin; Li Mei; Wang Zhengwen; Hu Sheng; Zhou Jun; Zhan Qiong</i>	
ELECTRICALLY RECONFIGURABLE ACTIVE METASURFACE FOR 3D DISTANCE RANGING	127
<i>Sun Il Kim; Junghyun Park; Byung Gil Jeong; Duhyun Lee; Jungwoo Kim; Changgyun Shin; Chang Bum Lee; Tatsuhiko Otsuka; Sangwook Kim; Ki-Yeon Yang; Yong-Young Park; Jisan Lee; Inoh Hwang; Jaeduck Jang; Kyounggho Ha; Hyuck Choo; Byoung Lyong Choi; Sung-Woo Hw</i>	
SINGLE-CHIP BEAM SCANNER WITH INTEGRATED LIGHT SOURCE FOR REAL-TIME LIGHT DETECTION AND RANGING	131
<i>Jisan Lee; Dongjae Shin; Bongyong Jang; Hyunil Byun; Changbum Lee; Changgyun Shin; Inoh Hwang; Dongshik Shim; Eunkyung Lee; Jinmyung Kim; Kyunghyun Son; Tatsuhiko Otsuka; Kyounggho Ha; Hyuck Choo</i>	
GE PHOTODIODE WITH -3 DB OE BANDWIDTH OF 110 GHZ FOR PIC AND EPIC PLATFORMS	135
<i>S. Lischke; A. Peczek; F. Korndörfer; C. Mai; H. Haisch; M. Koenigsmann; M. Rudisile; D. Steckler; F. Goetz; M. Fraschke; S. Marschmeyer; A. Krüger; Y. Yamamoto; D. Schmidt; U. Saarow; P. Heinrich; A. Kroh; M. A. Schubert; J. Katzer; P. Kulse; A. Trusch;</i>	
PROSPECTS FOR PHOTONIC IMPLEMENTATIONS OF NEUROMORPHIC DEVICES AND SYSTEMS	139
<i>B. J. Offrein; J. Geler-Kremer; J. Weiss; R. Dangel; P. Stark; A. Sharma; Stefan Abel; F. Horst</i>	
ON-CHIP PHASE CHANGE OPTICAL MATRIX MULTIPLICATION CORE	143
<i>Xuan Li; Nathan Youngblood; Wen Zhou; Johannes Feldmann; Jacob Swett; Samarath Aggarwal; A. Sebastian; C. David Wright; Wolfram Pernice; Harish Bhaskaran</i>	
THE MEMRISTOR LASER	147
<i>B. Tossoun; X. Sheng; J. P. Strachan; D. Liang</i>	
PLASMONICS: BREAKING THE BARRIERS OF SILICON PHOTONICS FOR HIGH-PERFORMANCE CHIP-TO-CHIP INTERCONNECTS	151
<i>Charles Lin; Divya Prasad; Saurabh Sinha; Brian Cline; Amr S. Helmy</i>	
GAN-ON-SI MM-WAVE RF DEVICES INTEGRATED IN A 200MM CMOS COMPATIBLE 3-LEVEL CU BEOL	155
<i>B. Parvais; A. Alian; U. Peralagu; R. Rodriguez; S. Yadav; A. Khaled; R. Y. Elkaslan; V. Putcha; A. Sibaja-Hernandez; M. Zhao; P. Wambacq; N. Collaert; N. Waldron</i>	

SUBSTRATE RF LOSSES AND NON-LINEARITIES IN GAN-ON-SI HEMT TECHNOLOGY	159
<i>S. Yadav; P. Cardinael; M. Zhao; K. Vondkar; A. Khaled; R. Rodriguez; B. Vermeersch; S. Makovejev; E. Ekoga; A. Pottrain; N. Waldron; J.-P. Raskin; B. Parvais; N. Collaert</i>	
GAN/ALN P-CHANNEL HFETS WITH $I_{MAX} > 420$ MA/MM AND ~ 20 GHZ f_T / f_{MAX}	163
<i>K. Nomoto; R. Chaudhuri; S. J. Bader; L. Li; A. Hickman; S. Huang; H. Lee; T. Maeda; H. W. Then; M. Radosavljevic; P. Fischer; A. Molnar; J. C. M. Hwang; H. G. Xing; D. Jena</i>	
$L_G = 19$ NM $IN_{0.8}GA_{0.2}AS$ COMPOSITE-CHANNEL HEMTS WITH $F_T = 738$ GHZ AND $F_{MAX} = 492$ GHZ	167
<i>Hyeon-Bhin Jo; Seung-Won Yun; Jun-Gyu Kim; Do-Young Yun; In-Geun Lee; Dae-Hyun Kim; Tae-Woo Kim; Sang-Kuk Kim; Jacob Yun; Ted Kim; Takuya Tsutsumi; Hiroki Sugiyama; Hideaki Matsuzaki</i>	
BALLISTIC MOBILITY AND INJECTION VELOCITY IN NANOSCALE INGAAS FINFETS	171
<i>Xiaowei Cai; Alon Vardi; Jesús Grajal; Jesús A. Del Alamo</i>	
A FAST WAFER LEVEL RELIABILITY (FWLR) MONITORING CONCEPT AS A CONTINUOUS RELIABILITY INDICATOR FOR WAFER MASS PRODUCTION	175
<i>A. Martin; A. Mitchell; M. Traving; S. Wegner; A. Norman-Elvenich; H. Mayr; H. Nielsen</i>	
A RELIABILITY ENHANCED 5NM CMOS TECHNOLOGY FEATURING 5TH GENERATION FINFET WITH FULLY-DEVELOPED EUV AND HIGH MOBILITY CHANNEL FOR MOBILE SOC AND HIGH PERFORMANCE COMPUTING APPLICATION	179
<i>J. C. Liu; S. Mukhopadhyay; Amit Kundu; S. H. Chen; H. C. Wang; D. S. Huang; J. H. Lee; M. I. Wang; Ryan Lu; S. S. Lin; Y. M. Chen; H. L. Shang; P. W. Wang; H. C. Lin; Geoffrey Yeap; Jun He</i>	
RELIABILITY ON EVOLUTIONARY FINFET CMOS TECHNOLOGY AND BEYOND	183
<i>Kihyun Choi; Hyun Chul Sagong; Minjung Jin; Jang Hai; Miji Lee; Taeyoung Jeong; Myung Soo Yeo; Hyewon Shim; Da Ahn; Wooyeon Kim; Yongjeung Kim; Junekyun Park; Hwasung Rhee; Euncheol Lee</i>	
CHARACTERIZATION SCHEME FOR PLASMA-INDUCED DEFECT CREATION DUE TO STOCHASTIC LATERAL STRAGGLING IN SI SUBSTRATES FOR ULTRA-LOW LEAKAGE DEVICES	187
<i>Y. Sato; T. Yamada; K. Nishimura; M. Yamasaki; M. Murakami; K. Urabe; K. Eriguchi</i>	
AN IMPROVED MODEL ON BURIED-OXIDE DAMAGE FOR TOTAL-IONIZING-DOSE EFFECT ON HV SOI LDMOS	191
<i>Zhangyi An Yuan; Ming Qiao; Xinjian Li; Xin Zhou; Zhaoji Li; Bo Zhang</i>	
MULTIPHONON-ELECTRON COUPLING ENHANCED DEFECT GENERATION AND BREAKDOWN MECHANISM IN MOL NEW SPACER DIELECTRICS FOR 7NM/5NM TECHNOLOGY NODES AND BEYOND	195
<i>Ernest Wu; Richard Southwick; Sanjay Mehta; Baozhen Li; Miaomiao Wang</i>	
CUSTOM SILICON AT FACEBOOK: A DATACENTER INFRASTRUCTURE PERSPECTIVE ON VIDEO TRANSCODING AND MACHINE LEARNING	199
<i>Prahlad Venkatapuram; Zhao Wang; Chandra Mallipeddi</i>	
MEMORY TECHNOLOGY: INNOVATIONS NEEDED FOR CONTINUED TECHNOLOGY SCALING AND ENABLING ADVANCED COMPUTING SYSTEMS	203
<i>Naga Chandrasekaran; Nirmal Ramaswamy; Chandra Mouli</i>	
MRAM IN MICROCONTROLLER AND MICROPROCESSOR PRODUCT APPLICATIONS	211
<i>Thomas Jew</i>	
28-NM 0.08 MM²/MB EMBEDDED MRAM FOR FRAME BUFFER MEMORY	215
<i>S. H. Han; J. M. Lee; H. M. Shin; J. H. Lee; K. S. Suh; K. T. Nam; B. S. Kwon; M. K. Cho; J. Lee; J. H. Jeong; J. H. Park; S. C. Oh; S. O. Park; S. H. Hwang; S. Pyo; H. T. Jung; Y. Ji; J. H. Bak; D. S. Kim; W. S. Ham; Y. J. Kim; K. Lee; Y. J. Song; G. H.</i>	
JEDEC-QUALIFIED HIGHLY RELIABLE 22NM FD-SOI EMBEDDED MRAM FOR LOW-POWER INDUSTRIAL-GRADE, AND EXTENDED PERFORMANCE TOWARDS AUTOMOTIVE-GRADE-1 APPLICATIONS	219
<i>V. B. Naik; K. Yamane; T. Y. Lee; J. Kwon; R. Chao; J. H. Lim; N. L. Chung; B. Behin-Aein; L. Y. Hau; D. Zeng; Y. Otani; C. Chiang; Y. Huang; L. Pu; S. H. Jang; W. P. Neo; H. Dixit; S. K. L. C. Goh; E. H. Toh; T. Ling; J. Hwang; J. W. Ting; R. Low; L. Zhan</i>	
A REFLOW-CAPABLE, EMBEDDED 8MB STT-MRAM MACRO WITH 9NS READ ACCESS TIME IN 16NM FINFET LOGIC CMOS PROCESS	223
<i>Yi-Chun Shih; Chia-Fu Lee; Yen-An Chang; Po-Hao Lee; Hon-Jarn Lin; Yu-Lin Chen; Chieh-Pu Lo; Ku-Feng Lin; Tien-Wei Chiang; Yuan-Jen Lee; Kuei-Hung Shen; Roger Wang; Wayne Wang; Harry Chuang; Eric Wang; Yu-Der Chih; Jonathan Chang</i>	
A 14 NM EMBEDDED STT-MRAM CMOS TECHNOLOGY	227
<i>D. Edelstein; M. Rizzolo; D. Sil; A. Dutta; J. Debrosse; M. Wordeman; A. Arceo; I. C. Chu; J. Demarest; E. R. J. Edwards; E. R. Everts; J. Fullam; A. Gasasira; G. Hu; M. Iwatake; R. Johnson; V. Katragadda; T. Levin; J. Li; Y. Liu; C. Long; T. Maffitt; S.</i>	
ADVANCED MTJ STACK ENGINEERING OF STT-MRAM TO REALIZE HIGH SPEED APPLICATIONS	231
<i>T. Y. Lee; K. Yamane; Y. Otani; D. Zeng; J. Kwon; J. H. Lim; V. B. Naik; L. Y. Hau; R. Chao; N. L. Chung; T. Ling; S. H. Jang; L. C. Goh; J. Hwang; L. Zhang; R. Low; N. Balasankaran; F. Tan; J. W. Ting; J. Chang; C. S. Seet; S. Ong; Y. S. You; S. T. Woo;</i>	
HIGH DRIVE AND LOW LEAKAGE CURRENT MBC FET WITH CHANNEL THICKNESS 1.2NM/0.6NM	235
<i>Xiaohe Huang; Chunsen Liu; Zhaowu Tang; Senfeng Zeng; Liwei Liu; Xiang Hou; Huawei Chen; Jiayi Li; Yu-Gang Jiang; David Wei Zhang; Peng Zhou</i>	
3D INTEGRATION OF VERTICAL-STACKING OF MOS; AND SI CMOS FEATURING EMBEDDED 2T1R CONFIGURATION DEMONSTRATED ON FULL WAFERS	239
<i>C. J. Su; M. K. Huang; K. S. Lee; V. P. H. Hu; Y. F. Huang; B. C. Zheng; C. H. Yao; N. C. Lin; K. H. Kao; T. C. Hong; P. J. Sung; C. T. Wu; T. Y. Yu; K. L. Lin; Y. C. Tseng; C. L. Lin; Y. J. Lee; T. S. Chao; J. Y. Li; W. F. Wu; J. M. Shieh; Y. H. Wang; W.</i>	
0.5T0.5R - INTRODUCING AN ULTRA-COMPACT MEMORY CELL ENABLED BY SHARED GRAPHENE EDGE-CONTACT AND H-BN INSULATOR	243
<i>Chao-Hui Yeh; Dujiao Zhang; Wei Cao; Kaustav Banerjee</i>	

SCALING MOS₂ NCFET TO 83 NM WITH RECORD-LOW RATIO OF SS_{AVE}/SS_{REF}=0.177 AND MINIMUM 20 MV HYSTERESIS	247
<i>Guanhua Yang; Jiebin Niu; Congyan Lu; Rongrong Cao; Jiawei Wang; Ying Zhao; Xichen Chuai; Mengmeng Li; Di Geng; Nianduan Lu; Qi Liu; Ling Li; Ming Liu</i>	
MONOLAYER MOS; STEEP-SLOPE TRANSISTORS WITH RECORD-HIGH SUB-60-MV/DECADE CURRENT DENSITY USING DIRAC-SOURCE ELECTRON INJECTION	251
<i>Maomao Liu; Hemendra Nath Jaiswal; Simran Shahi; Sichen Wei; Yu Fu; Chaoran Chang; Anindita Chakravarty; Fei Yao; Huamin Li</i>	
THE DEMONSTRATION OF CARBON NANO-TUBES (CNTS) AS A PROMISING HIGH ASPECT RATIO (>25) THROUGH SILICON VIAS (TSVS) MATERIAL FOR THE VERTICAL CONNECTION IN THE HIGH DENSE 3DICS	255
<i>P.-Y. Lu; C.-M. Yen; S.-Y. Chang; Y.-J. Feng; C. Lien; C.-W. Hu; C.-W. Yao; M.-H. Lee; M.-H. Liao</i>	
THERMAL MODELING OF 3D POLYLITHIC INTEGRATION AND IMPLICATIONS ON BEOL RRAM PERFORMANCE	259
<i>Ankit Kaul; Xiaochen Peng; Sreejith Kochupurackal Rajan; Shimeng Yu; Muhammad S. Bakir</i>	
ATOMIC-DEVICE HYBRID MODELING OF RELAXATION EFFECT IN ANALOG RRAM FOR NEUROMORPHIC COMPUTING	263
<i>Feng Xu; Bin Gao; Yue Xi; Jianshi Tang; Huaqiang Wu; He Qian</i>	
MODELING OF VIRGIN STATE AND FORMING OPERATION IN EMBEDDED PHASE CHANGE MEMORY (PCM)	267
<i>M. Baldo; O. Melnic; M. Scuderi; G. Nicotra; M. Borghi; E. Petroni; A. Motta; P. Zuliani; A. Redaelli; D. Ielmini</i>	
TECHNOLOGY-ARRAY-ALGORITHM CO-OPTIMIZATION OF RRAM FOR STORAGE AND NEUROMORPHIC COMPUTING; DEVICE NON-IDEALITIES AND THERMAL CROSS-TALK	271
<i>Yimao Cai; Zongwei Wang; Zhizhen Yu; Yaotian Ling; Qingyu Chen; Yunfan Yang; Shengyu Bao; Lindong Wu; Lin Bao; Runsheng Wang; Ru Huang</i>	
TCAD DEVICE TECHNOLOGY CO-OPTIMIZATION WORKFLOW FOR MANUFACTURABLE MRAM TECHNOLOGY	275
<i>Hemant Dixit; Vinayak Bharat Naik; Kazutaka Yamane; Taeyoung Lee; Jae-Hyun Kwon; Behtash Behin-Aein; Steven Soss; William J. Taylor</i>	
SPIN-ORBIT-TORQUE MATERIAL EXPLORATION FOR MAXIMUM ARRAY-LEVEL READ/WRITE PERFORMANCE	279
<i>Yu-Ching Liao; Piyush Kumar; Mahendra Dc; Xiang Li; Delin Zhang; Jian-Ping Wang; Shan X. Wang; Daniel C. Ralph; A. Naeemi</i>	
NEURO-ELECTRONIC DEVICES AND NANOTOOLS TO INTERACT WITH NEURONAL NETWORKS	283
<i>S. Martinoa; A. Andolfi; L. Muzzi; M. Pisano; A. Spanu; R. Raiteri</i>	
THIN-FILM TRANSISTOR PLATFORM FOR ELECTROPHYSIOLOGICAL AND ELECTROCHEMICAL CHARACTERIZATION OF BIOLOGICAL CELLS	287
<i>A.-C. Eiler; P.-M. Faure; J. Sugita; S. Ihida; D. Zhu; Y. Sakai; K. Fujiu; K. Komori; H. Toshiyoshi; A. Tixier-Mita</i>	
HIGH-RESOLUTION NEUROSTIMULATION AND OPTOGENETIC ELECTROPHYSIOLOGY WITH PEDOT:PSS-COATED GRAPHENE	291
<i>F. Sun; Z. Xiong; J. Park; G. Xu</i>	
FLEXIBLE BOOTSTRAPPED CASCADE SYSTEM WITH FEEDBACK FOR CAPACITIVE THROUGH-SUBSTRATE ELECTRIC POTENTIAL MEASUREMENTS WITH A 55 DB RELATIVE GAIN	295
<i>J. C. Costa; A. Pouryazdan; R. J. Prance; H. Prance; N. Münzenrieder</i>	
NANOPHOTONIC SENSOR IMPLANTS WITH 3D HYBRID PERIODIC-AMORPHOUS PHOTONIC CRYSTALS FOR WIDE-ANGLE MONITORING OF LONG-TERM IN-VIVO INTRAOCULAR PRESSURE	299
<i>R. H. Siddique; L. Liedtke; H. Park; S. Y. Lee; H. Raniwala; D. Y. Park; D. H. Lim; H. Choo</i>	
A HIGH-DENSITY LOGIC-ON-LOGIC 3DIC DESIGN USING FACE-TO-FACE HYBRID WAFER-BONDING ON 12NM FINFET PROCESS	303
<i>S. Sinha; S. Hung; D. Fisher; X. Xu; C. Chao; P. Chandupatla; F. Frederick; H. Perry; D. Smith; A. Cestero; J. Safran; V. Ayyavu; M. Bhargava; R. Mathur; D. Prasad; R. Katz; A. Kinsbruner; J. Garant; J. Lubguban; S. Knickerbocker; V. Soler; B. Cline; R. Ch</i>	
3D-OPTIMIZED SRAM MACRO DESIGN AND APPLICATION TO MEMORY-ON-LOGIC 3D-IC AT ADVANCED NODES	307
<i>R. Chen; P. Wecks; S. M. Salahuddin; S.-W. Kim; G. Sisto; G. Van Der Plas; M. Stucchi; R. Baert; P. Debacker; M. H. Na; J. Ryckaert; D. Milojevic; E. Beyne</i>	
HOW 3D INTEGRATION TECHNOLOGIES ENABLE ADVANCED COMPUTE NODE FOR EXASCALE-LEVEL HIGH PERFORMANCE COMPUTING?	311
<i>D. Dutoit; P. Coudrain; P.-Y. Martinez; P. Vivet; J. Charbonnier; A. Garnier; D. Lattard; S. Chéramy; E. Guthmuller; A. Philippe; Y. Thonnart; F. Clermidy</i>	
SYSTEM EXPLORATION AND TECHNOLOGY DEMONSTRATION OF 3D WAFER-TO-WAFER INTEGRATED STT-MRAM BASED CACHES FOR ADVANCED MOBILE SOCS	315
<i>M. Perumkunnil; F. Yasin; S. Rao; S. M. Salahuddin; D. Milojevic; G. Van Der Plas; J. Ryckaert; Eric Beyne; A. Furnémont; G. S. Kar</i>	
FIRST DEMONSTRATION OF HETEROGENOUS COMPLEMENTARY FETS UTILIZING LOW-TEMPERATURE (200 °C) HETERO-LAYERS BONDING TECHNIQUE (LT-HBT)	319
<i>T.-Z. Hong; W.-H. Chang; A. Agarwal; Y.-T. Huang; C.-Y. Yang; T.-Y. Chu; H.-Y. Chao; Y. Chuang; S.-T. Chung; J.-H. Lin; S.-M. Luo; C.-J. Tsai; M.-J. Li; X.-R. Yu; N.-C. Lin; T.-C. Cho; P.-J. Sung; C.-J. Su; G.-L. Luo; F.-K. Hsueh; K.-L. Lin; H. Ishii; T.</i>	
LOW TEMPERATURE AND ION-CUT BASED MONOLITHIC 3D PROCESS INTEGRATION PLATFORM INCORPORATED WITH CMOS, RRAM AND PHOTO-SENSOR CIRCUITS	323
<i>Hoonhee Han; Rino Choi; Seong-Ook Jung; Sung Woo Chung; Byung Jin Cho; S. C. Song; Changhwan Choi</i>	

A 4.6μM, 512\times512, ULTRA-LOW POWER STACKED DIGITAL PIXEL SENSOR WITH TRIPLE QUANTIZATION AND 127DB DYNAMIC RANGE	327
<i>Chiao Liu; Lyle Bainbridge; Andrew Berkovich; Song Chen; Wei Gao; Tsung-Hsun Tsai; Kazuya Mori; Rimon Ikeno; Masayuki Uno; Toshiyuki Isozaki; Yu-Lin Tsai; Isao Takayanagi; Junichi Nakamura</i>	
A 0.8 μM NONACELL FOR 108 MEGAPIXELS CMOS IMAGE SENSOR WITH FD-SHARED DUAL CONVERSION GAIN AND 18,000E- FULL-WELL CAPACITANCE.....	331
<i>Youngsun Oh; Munhwan Kim; Wonchul Choi; Hana Choi; Honghyun Jeon; Junho Seok; Yujung Choi; Jaejin Jung; Kwisung Yoo; Donghyuk Park; Yitae Kim; Kyung-Min Koh; Jesuk Lee; Chang-Rok Moon; Jungchak Ahn</i>	
A 64M CMOS IMAGE SENSOR USING 0.7UM PIXEL WITH HIGH FWC AND SWITCHABLE CONVERSION GAIN.....	335
<i>Y. Jay Jung; Vincent C. Venezia; Sangjoo Lee; Chun Yung Ai; Yibo Zhu; King W. Yeung; Geunsook Park; Woonil Choi; Zhiqiang Lin; Wu-Zang Yang; Alan Chih-Wei Hsiung; Lindsay Grant</i>	
A GLOBAL SHUTTER WIDE DYNAMIC RANGE SOFT X-RAY CMOS IMAGE SENSOR WITH BSI PINNED PHOTODIODE, TWO-STAGE LOFIC AND VOLTAGE DOMAIN MEMORY BANK.....	339
<i>H. Shike; R. Kuroda; R. Kobayashi; M. Murata; Y. Fujihara; M. Suzuki; T. Shibaguchi; N. Kuriyama; J. Miyawaki; T. Harada; Y. Yamasaki; T. Watanabe; Y. Harada; S. Sugawa</i>	
IMAGING IN SHORT-WAVE INFRARED WITH 1.82 μM PIXEL PITCH QUANTUM DOT IMAGE SENSOR	343
<i>Jiwon Lee; Epimitheas Georgitzikis; Yunlong Li; Ziduo Lin; Jihoon Park; Itai Lieberman; David Cheyns; Murali Jayapala; Andy Lambrechts; Steven Thijs; Richard Stahl; Pawel E. Malinowski</i>	
A BACK ILLUMINATED 10μM SPAD PIXEL ARRAY COMPRISING FULL TRENCH ISOLATION AND CU-CU BONDING WITH OVER 14% PDE AT 940NM.....	347
<i>K. Ito; Y. Otake; Y. Kitano; A. Matsumoto; J. Yamamoto; T. Ogasahara; H. Hiyama; R. Naito; K. Takeuchi; T. Tada; K. Takabayashi; H. Nakayama; K. Tatani; T. Hirano; T. Wakano</i>	
PORTABLE MULTI-SPECTRAL IMAGING: DEVICES, VERTICAL INTEGRATION, AND APPLICATIONS.....	351
<i>Alberto Valdes-Garcia; Petar Pepeljovski; Ivan Duran; Jean-Olivier Plouchart; Mark Yeck; Huijuan Liu</i>	
MILLIMETER-WAVE BAND CMOS RF PHASED-ARRAY TRANSCEIVER IC DESIGNS FOR 5G APPLICATIONS.....	355
<i>H.-C. Park; D. Kang; J. Lee; D. Minn; Y. Aoki; K. Kim; S. Lee; D. Lee; S. Kim; J. Kim; W. Lee; C. Kim; S. Park; J. Park; B. Suh; J. Jang; M. Kim; K. Min; S. Jeon; A.-S. Ryu; Y. Kim; J. H. Lee; J. Son; S.-G. Yang</i>	
SI AND SOI CMOS TECHNOLOGIES FOR MILLIMETER WAVE WIRELESS APPLICATIONS	359
<i>B. Martineau; D. Belot</i>	
MMWAVE AND SUB-THZ TECHNOLOGY DEVELOPMENT IN INTEL 22NM FINFET (22FFL) PROCESS	363
<i>Qiang Yu; Said Rami; James Waldemer; Yunzhe Ma; Vijaya Neeli; Jeffrey Garrett; Guannan Liu; Jabeom Koo; Mauricio Marulanda; Saurabh Morarka; Surej Ravikumar; Yi-Shin Yeh; Jessica Chou; Thomas Brown; Triveni Rane; Carlos Nieva; Dyan Ali; Sameer Joglekar; M</i>	
ORGANIC PACKAGE SUBSTRATES USING LITHOGRAPHIC VIA TECHNOLOGY FOR RF TO THZ APPLICATIONS.....	367
<i>A. Aleksov; G. Dogiamis; T. Kamgaing; A. Elsherbini; J. Swan; K. Darmawikarta; S. Boyapati; J. Holloway; R. Han</i>	
SURFACE WAVE AND LAMB WAVE ACOUSTIC DEVICES ON HETEROGENOUS SUBSTRATE FOR 5G FRONT-ENDS	371
<i>Hongyan Zhou; Shibin Zhang; Zhongxu Li; Kai Huang; Pengcheng Zheng; Jinbo Wu; Chen Shen; Liping Zhang; Tianguai You; Lianghui Zhang; Kang Liu; Huarui Sun; Hongtao Xu; Xiaomeng Zhao; Xin Ou</i>	
HFO₂-BASED FEFET AND FTJ FOR FERROELECTRIC-MEMORY CENTRIC 3D LSI TOWARDS LOW-POWER AND HIGH-DENSITY STORAGE AND AI APPLICATIONS.....	375
<i>Masumi Saitoh; Reika Ichihara; Marina Yamaguchi; Kunifumi Suzuki; Keisuke Takano; Keisuke Akari; Kota Takahashi; Yuta Kamiya; Kazuhiro Matsuo; Yuuichi Kamimuta; Kivamu Sakuma; Kensuke Ota; Shosuke Fujii</i>	
IMPLICATION OF CHANNEL PERCOLATION IN FERROELECTRIC FETS FOR THRESHOLD VOLTAGE SHIFT MODELING.....	379
<i>Y. Xiang; M. Garcia Bardon; B. Kaczer; Md N. K. Alam; L.-A. Ragnarsson; G. Groeseneken; J. Van Houdt</i>	
A NOVEL HYBRID HIGH-SPEED AND LOW POWER ANTIFERROELECTRIC HSO BOOSTED CHARGE TRAP MEMORY FOR HIGH-DENSITY STORAGE.....	383
<i>T. Ali; K. Mertens; R. Olivo; M. Rudolph; S. Oehler; K. Kühnel; D. Lehninger; F. Müller; M. Lederer; R. Hoffmann; P. Schramm; K. Biedermann; Alireza M. Kia; J. Metzger; R. Binder; M. Czernohorsky; T. Kämpfe; J. Müller; K. Seidel; J. Van Houdt; L. M. Eng</i>	
IMPACT OF OXYGEN VACANCY CONTENT IN FERROELECTRIC HZO FILMS ON THE DEVICE PERFORMANCE.....	387
<i>T. Mittmann; M. Materano; S.-C. Chang; I. Karpov; T. Mikolajick; U. Schroeder</i>	
HIGH SPEED MEMORY OPERATION IN CHANNEL-LAST, BACK-GATED FERROELECTRIC TRANSISTORS	391
<i>Abhishek A. Sharma; Brian Doyle; Hui Jae Yoo; I-Cheng Tung; Jack Kavalieros; Matthew V. Metz; Miriam Reshotko; Prashant Majhi; Tobias Brown-Heft; Yu-Jin Chen; Van H. Le</i>	
APPLICATION AND BENEFITS OF TARGET PROGRAMMING ALGORITHMS FOR FERROELECTRIC HFO₂ TRANSISTORS.....	395
<i>H. Zhou; J. Ocker; A. Padovani; M. Pesic; M. Trentzsch; S. Dünkel; H. Mulaosmanovic; S. Slesazek; Luca Larcher; S. Beyer; S. Müller; T. Mikolajick</i>	
SYMBIOSIS OF SEMICONDUCTORS, AI AND QUANTUM COMPUTING	399
<i>S. W. Hwang; S. Han; W. Lee; W. Chang; J. H. Song; S. J. Kim; S. Park; H. J. Shin; J. Heo; Y. S. Choi; T. Ha; D. Lee; H. Lee; J. Lee; R. Ashcraft; G. H. Koh; H. K. Kang</i>	
PERFORMANCE-POWER MANAGEMENT AWARE STATE-OF – THE-ART 5NM FINFET DESIGN(5LPE) WITH DUAL CPP FROM MOBILE TO HPC APPLICATION	405
<i>Jaehun Jeong; Young Gun Ko; Kihwang Son; Sung Won Kim; Ju Youn Kim; Jeongmin Choi; Hyungjong Lee; Ho Lee; Sihyung Lee; Chunghwan Shin; Heebum Hong; Sung-Il Jo; Youngho Lee; Byungha Choi; Jaechul Kim; Minseong Lee; Kyunghoon Jung; Yuri Yasuda-Masuoka; Jong</i>	

BURIED BITLINE FOR SUB-5NM SRAM DESIGN	409
<i>R. Mathur; M. Bhargava; S. Salahuddin; P. Schuddinck; J. Ryckaert; S. Annamalai; A. Gupta; Y. K. Chong; S. Sinha; B. Cline; J. P. Kulkarni</i>	
BURIED POWER RAIL SCALING AND METAL ASSESSMENT FOR THE 3 NM NODE AND BEYOND	413
<i>A. Gupta; O. Varela Pedreira; Z. Tao; H. Mertens; D. Radisic; N. Jourdan; K. Devriendt; N. Heylen; S. Wang; B. Chehab; D. Jang; G. Hellings; F. Sebaai; C. Lorant; L. Teugels; A. Peter; B. T. Chan; F. Schleicher; I. Demonie; P. Marien; A. Sepúlveda; O. Richard; N. Nagesh; A. Lesniewska; F. Lazzarino; J. Ryckaert; P. Morin; E. Altamirano-Sanchez; G. Murdoch; J. Bommels; S. Demuyck; M. H. Na; Z. Tokei; S. Biesemans; E. Dentoni Litta; N. Horiguchi</i>	
INTERCONNECT SCALING CHALLENGES, AND OPPORTUNITIES TO ENABLE SYSTEM-LEVEL PERFORMANCE BEYOND 30 NM PITCH	417
<i>Griselda Bonilla; N. Lanzillo; C.-K. Hu; C. J. Penny; A. Kumar</i>	
SUPERVIA PROCESS INTEGRATION AND RELIABILITY COMPARED TO STACKED VIAS USING BARRIERLESS RUTHENIUM	421
<i>V. Vega-Gonzalez; H. Puliyalil; J. Versluijs; A. Lesniewska; O. Varela-Pereira; R. Baert; S. Paolillo; S. Decoster; F. Schleicher; D. Montero; J. Bekaert; E. Kesters; Q. T. Le; C. Lorant; L. Teugels; N. Heylen; N. Jourdan; Z. El-Mekki; M. Van Der Veen; I. Ciofi; B. Briggs; J. Heijlen; L. Dupas; B. De-Wachter; E. Vancoille; T. Webers; H. Vats; L. Rynders; M. Cupak; J. Uk-Lee; Y. Drissi; L. Halipre; A.-L. Charley; P. Verdonck; T. Witters; S. V. Gompel; Y. Kimura; I. Demonie; F. Lazzarino; M. Ercken; R. Kim; D. Trivkovic; K. Croes; M. Jaysankar; C. Wilson; G. Muroch; Z. Tokei</i>	
3-D SELF-ALIGNED STACKED NMOS-ON-PMOS NANORIBBON TRANSISTORS FOR CONTINUED MOORE'S LAW SCALING	425
<i>C.-Y. Huang; G. Dewey; E. Mannebach; A. Phan; P. Morrow; W. Rachmady; I.-C. Tung; N. Thomas; U. Alaani; R. Paul; N. Kabir; B. Krist; A. Oni; M. Mehta; M. Harper; P. Nguyen; R. Keech; S. Vishwanath; K. L. Cheong; J. S. Kang; A. Lilak; M. Metz; S. Clendenn</i>	
VERTICAL GATE-ALL-AROUND TUNNEL FETS USING INGAAS NANOWIRE/SI WITH CORE-MULTISHELL STRUCTURE	429
<i>Katsuhiro Tomioka; Hironori Gamo; Junichi Motohisa; Takashi Fukui</i>	
VERTICAL NV-NEM SWITCHES IN CMOS BACK-END-OF-LINE: FIRST EXPERIMENTAL DEMONSTRATION AND ARRAY PROGRAMMING SCHEME	433
<i>U. Sikder; L. P. Tatum; T.-T. Yen; T.-J. K. Liu</i>	
A NOVEL SUPER-STEEP SLOPE (~0.015MV/DEC) GATE-CONTROLLED THYRISTOR (GCT) FUNCTIONAL MEMORY DEVICE TO SUPPORT THE INTEGRATE-AND-FIRE CIRCUIT FOR SPIKING NEURAL NETWORKS	437
<i>Cheng-Lin Sung; Hang-Ting Lue; Ming-Liang Wei; Shu-Yin Ho; Han-Wen Hu; Pei-Ying Du; Wei-Chen Chen; Chieh Roger Lo; Teng-Hao Yeh; Keh-Chung Wang; Chih-Yuan Lu</i>	
DYNAMICS OF HFZRO₂ FERROELECTRIC STRUCTURES: EXPERIMENTS AND MODELS	441
<i>Taekyong Kim; Jesús A. Del Alamo; Dimitri A. Antoniadis</i>	
ALL-ELECTRICAL CONTROL OF SCALED SPIN LOGIC DEVICES BASED ON DOMAIN WALL MOTION	445
<i>E. Raymenants; D. Wan; S. Couet; L. Souriau; A. Thiam; D. Tsvetanova; Y. Carvel; I. Asselberghs; M. Heyns; D. E. Nikonov; I. A. Young; S. Pizzini; V. D. Nguyen; I. P. Radu</i>	
APPLICABILITY OF SHOCKLEY-READ-HALL THEORY FOR INTERFACE STATES	449
<i>Bernhard Ruch; Markus Jech; Gregor Pobegen; Tibor Grasser</i>	
DESIGN PRINCIPLE OF CHANNEL MATERIAL FOR OXIDE-SEMICONDUCTOR FIELD-EFFECT TRANSISTOR WITH HIGH THERMAL STABILITY AND HIGH ON-CURRENT BY FLUORINE DOPING	453
<i>H. Kawai; H. Fujiwara; J. Kataoka; N. Saito; T. Ueda; T. Enda; T. Ishihara; K. Ikeda</i>	
LARGE SCALE PLANE-WAVE BASED DENSITY-FUNCTIONAL THEORY SIMULATIONS FOR ELECTRONIC DEVICES	457
<i>L. W. Wang; M. Ye; Y. Y. Liu; X. W. Jiang</i>	
COLD SOURCE ENGINEERING TOWARDS SUB-60MV/DEC P-TYPE FIELD-EFFECT-TRANSISTORS (PFETS): MATERIALS, STRUCTURES, AND DOPING OPTIMIZATIONS	461
<i>Qianwen Wang; Pengpeng Sang; Xiaolei Ma; Fei Wang; Wei Wei; Weiqiang Zhang; Yuan Li; Jiechi Chen</i>	
INTRODUCING 2D-FETS IN DEVICE SCALING ROADMAP USING DTCO	465
<i>Z. Ahmed; A. Afzalian; T. Schram; D. Jang; D. Verreck; Q. Smets; P. Schuddinck; B. Chehab; S. Sutar; G. Aruchelvan; A. Soussou; I. Asselberghs; A. Spessot; I. P. Radu; B. Parvais; J. Ryckaert; M. H. Na</i>	
A NEW SURFACE POTENTIAL BASED COMPACT MODEL FOR INDEPENDENT DUAL GATE A-IGZO TFT: EXPERIMENTAL VERIFICATION AND CIRCUIT DEMONSTRATION	469
<i>Jingrui Guo; Ying Zhao; Guanhua Yang; Xichen Chuai; Wenhao Lu; Dongyang Liu; Qian Chen; Xinlv Duan; Shijie Huang; Yue Su; Di Geng; Nianduan Lu; Tao Cui; Jin Jang; Ling Li; Ming Liu</i>	
E-MODE P-GAN GATE HEMT WITH P-FET BRIDGE FOR HIGHER V_{TH} AND ENHANCED V_{TH} STABILITY	473
<i>Mengyuan Hua; Junting Chen; Chengcai Wang; Ling Liu; Lingling Li; Junlei Zhao; Zuoheng Jiang; Jin Wei; Li Zhang; Zheyang Zheng; Kevin J. Chen</i>	
1.2 KV VERTICAL GAN FIN JFETS WITH ROBUST AVALANCHE AND FAST SWITCHING CAPABILITIES	477
<i>J. Liu; M. Xiao; Y. Zhang; S. Pidaparthy; H. Cui; A. Edwards; L. Baubutr; W. Meier; C. Coles; C. Drowley</i>	
DYNAMIC BREAKDOWN VOLTAGE OF GAN POWER HEMTS	481
<i>R. Zhang; J. P. Kozak; Q. Song; M. Xiao; J. Liu; Y. Zhang</i>	
GATE OXIDE INSTABILITY AND LIFETIME IN SIC MOSFETS UNDER A WIDE RANGE OF POSITIVE ELECTRIC FIELD STRESS	485
<i>M. Noguchi; A. Koyama; T. Iwamatsu; H. Amishiro; H. Watanabe; N. Miura</i>	
A NOVEL INSIGHT ON INTERFACE TRAPS DENSITY (DIT) EXTRACTION IN GAN-ON-SI MOS-C HEMTS	489
<i>W. Vandendael; S. Martin; M.-A. Jaud; A. Krakovinsky; L. Vauche; C. Le Royer; J. Biscarrat; A. G. Viey; R. Gwoziecki; R. Modica; F. Iucolano; M. Plissonnier; F. Gaillard</i>	

CARBON-RELATED PBTI DEGRADATION MECHANISMS IN GAN-ON-SI E-MODE MOSC-HEMT	493
<i>A. G. Viey; W. Vandendaele; M.-A. Jaud; L. Gerrer; X. Garros; J. Cluzel; S. Martin; A. Krakovinsky; J. Biscarrat; R. Gwoziecki; M. Plissomier; F. Gaillard; R. Modica; F. Iucolano; M. Meneghini; G. Meneghesso; G. Ghibardo</i>	
ADVANCED TECHNOLOGY AND SYSTEMS OF CROSS POINT MEMORY	497
<i>Albert Fazio</i>	
HIGH DENSITY EMBEDDED PCM CELL IN 28NM FDSOI TECHNOLOGY FOR AUTOMOTIVE MICRO-CONTROLLER APPLICATIONS	501
<i>F. Arnaud; P. Ferreira; F. Piazza; A. Gandolfo; P. Zuliani; P. Mattavelli; E. Gomiero; G. Samanni; J. Jasse; C. Jahan; J. P. Reynard; R. Berthelon; O. Weber; A. Villaret; B. Dumont; J. C. Grenier; R. Ranica; C. Gallon; C. Boccaccio; A. Souhaite; L. Desvoi</i>	
FIRST DEMONSTRATION OF OXRRAM INTEGRATION ON 14NM FINFET PLATFORM AND SCALING POTENTIAL ANALYSIS TOWARDS SUB-10NM NODE	505
<i>Xiaoxin Xu; Jie Yu; Tiancheng Gong; Jianguo Yang; Jiahao Yin; Da Nian Dong; Qing Luo; Jing Liu; Zhaoan Yu; Qi Liu; Hangbing Lv; Ming Liu</i>	
DEMONSTRATION OF NARROW SWITCHING DISTRIBUTIONS IN STTMRAM ARRAYS FOR LLC APPLICATIONS AT 1X NM NODE	509
<i>E. R. J. Edwards; G. Hu; S. L. Brown; C. P. D'Emic; M. G. Gottwald; P. Hashemi; H. Jung; J. Kim; G. Lauer; J. J. Nowak; J. Z. Sun; T. Suwannasiri; P. L. Trouilloud; S. Woo; D. C. Worledge</i>	
HIGH-DENSITY SOT-MRAM TECHNOLOGY AND DESIGN SPECIFICATIONS FOR THE EMBEDDED DOMAIN AT 5NM NODE	513
<i>M. Gupta; M. Perumkunnil; K. Garello; S. Rao; F. Yasin; G. S. Kar; A. Furnémont</i>	
HIGH-PERFORMANCE SHAPE-ANISOTROPY MAGNETIC TUNNEL JUNCTIONS DOWN TO 2.3 NM	517
<i>B. Jinnai; J. Igarashi; K. Watanabe; T. Funatsu; H. Sato; S. Fukami; H. Ohno</i>	
CMOS CRYO-ELECTRONICS FOR QUANTUM COMPUTING	521
<i>J. Crainckx; A. Potocnik; B. Parvais; A. Grill; S. Narasimhamoorthy; S. Van Winckel; S. Brebels; M. Mongillo; R. Li; B. Govoreanu; I. Radu</i>	
CRYO-CMOS INTERFACES FOR LARGE-SCALE QUANTUM COMPUTERS	525
<i>F. Sebastiano; J. P. G. Van Dijk; P. A. 't Hart; B. Patra; J. Van Staveren; X. Xue; C. G. Almudever; G. Scappucci; M. Veldhorst; L. M. K. Vandersypen; A. Vladimirescu; S. Pellerano; M. Babaie; E. Charbon</i>	
CRYO-CMOS COMPACT MODELING	529
<i>Christian Enz; Arnout Beckers; Farzan Jazaeri</i>	
CHIP DESIGN FOR FUTURE GRAVITATIONAL WAVE DETECTORS	533
<i>F. Tavernier; A. Gatti; C. Barretto</i>	
A LOW-POWER CMOS QUANTUM CONTROLLER FOR TRANSMON QUBITS	537
<i>J. C. Bardin</i>	
III-V HEMTS FOR CRYOGENIC LOW NOISE AMPLIFIERS	541
<i>J. Grahm; E. Cha; A. Pourkabirian; J. Stenarson; N. Wadefalk</i>	
SUPERCONDUCTIVE SINGLE FLUX QUANTUM LOGIC DEVICES AND CIRCUITS: STATUS, CHALLENGES, AND OPPORTUNITIES	545
<i>Massoud Pedram</i>	
PHONON-BLOCKED JUNCTION REFRIGERATORS FOR CRYOGENIC QUANTUM DEVICES	549
<i>E. Mykkänen; J. S. Lehtinen; A. Ronzani; A. Kemppinen; A. Alkurdi; P.-O. Chappuis; M. Prunnila</i>	
SUB-10MK-RESOLUTION THERMAL-BOLOMETRIC INTEGRATED FET-TYPE SENSORS BASED ON LAYERED BI₂O₃SE SEMICONDUCTOR NANOSHEETS	553
<i>Qifeng Cai; Shuo Liu; Minzhi Du; Lei Xu; Chunyan Zhao; Congwei Tan; Teng Tu; Kun Zhang; Hailin Peng; Xing Zhang; Ming Li; Ming He; Ru Huang</i>	
FUNCTIONAL METAMATERIAL DEVICES ENABLED BY MICROSYSTEMS	557
<i>X. Zhang; X. Zhao</i>	
ENERGY HARVESTING IN THE BACK-END OF LINE WITH CMOS COMPATIBLE FERROELECTRIC HAFNIUM OXIDE	561
<i>C. Mart; S. Abdulazhanov; M. Czernohorsky; T. Kämpfe; D. Lehniger; K. Falidas; S. Eßlinger; K. Kühnel; S. Oehler; M. Rudolph; M. Wiatr; S. Kolodinski; R. Seidel; W. Weinreich; L. M. Eng</i>	
SELF-TEMPERATURE-COMPENSATED GAN MEMS RESONATORS THROUGH STRAIN ENGINEERING UP TO 600 K	565
<i>L. Sang; H. Sun; X. Yang; T. Li; B. Shen; M. Liao</i>	
HIGHLY SENSITIVE AMPLIFIER CIRCUIT CONSISTING OF COMPLEMENTARY PFET-TYPE AND RESISTOR-TYPE GAS SENSORS	569
<i>Yujeong Jeong; Wonjun Shin; Seongbin Hong; Gyuweon Jung; Jinwoo Park; Dongkyu Jang; Donghee Kim; Dongseok Kwon; Byung-Gook Park; Jong-Ho Lee</i>	
PLANAR GAN POWER INTEGRATION – THE WORLD IS FLAT	573
<i>Kevin J. Chen; Jin Wei; Gaofei Tang; Han Xu; Zheyang Zheng; Li Zhang; Wenjie Song</i>	
PROGRESSING -190 °C TO +500 °C DURABLE SIC JFET ICS FROM MSI TO LSI	577
<i>P. Neudeck; D. Spry; M. Krasowski; L. Chen; N. Prokop; L. Greer; C. Chang</i>	
ADVANCES IN RESEARCH ON 300MM GALLIUM NITRIDE-ON-SI(111) NMOS TRANSISTOR AND SILICON CMOS INTEGRATION	581
<i>Han Wui Then; M. Radosavljevic; N. Desai; R. Ehlert; V. Hadagali; K. Jun; P. Koirala; N. Minutillo; R. Kotlyar; A. Oni; M. Qayyum; J. Rode; J. Sandford; T. Talukdar; N. Thomas; H. Vora; P. Wallace; M. Weiss; X. Weng; P. Fischer</i>	
GAN POWER ICS: REVIEWING STRENGTHS, GAPS, AND FUTURE DIRECTIONS	585
<i>O. Trescases; S. K. Murray; W. L. Jiang; M. S. Zaman</i>	
MONOLITHIC GAN POWER IC TECHNOLOGY DRIVES WIDE BANDGAP ADOPTION	589
<i>Dan Kinzer</i>	

GATE DRIVE CONCEPT FOR DV/DT CONTROL OF GAN GIT-BASED MOTOR DRIVE INVERTERS	593
<i>E. Persson; D. Wilhelm</i>	
APPLICATION OF WBG POWER DEVICES IN FUTURE 3-ϕ VARIABLE SPEED DRIVE INVERTER SYSTEMS: "HOW TO HANDLE A DOUBLE-EDGED SWORD"	597
<i>J. W. Kolar; J. Azurza Anderson; S. Miric; M. Haider; M. Guacci; M. Antivachis; G. Zulauf; D. Menzi; P. S. Niklaus; J. Miniböck; P. Papamanolis; G. Rohner; N. Nain; D. Cittanti; D. Bortis</i>	
A 16 KV PV INVERTER USING SERIES-CONNECTED 10 KV SIC MOSFET DEVICES	601
<i>R. Burgos; D. Dong; X. Lin; L. Ravi</i>	
ANTI-FERROELECTRIC HF_xZR_{1-x}O₂ CAPACITORS FOR HIGH-DENSITY 3-D EMBEDDED-DRAM	605
<i>Sou-Chi Chang; Nazila Haratipour; Shriram Shivaraman; Tobias L. Brown-Heft; Jason Peck; Chia-Ching Lin; I-Cheng Tung; Devin R. Merrill; Huiying Liu; Che-Yun Lin; Fatih Hamzaoglu; Matthew V. Metz; Ian A Young; Jack Kavalieros; Uygur E. Avcı</i>	
CAPACITOR-LESS, LONG-RETENTION (>400S) DRAM CELL PAVING THE WAY TOWARDS LOW-POWER AND HIGH-DENSITY MONOLITHIC 3D DRAM	609
<i>A. Belmonte; H. Oh; N. Rassoul; G. L. Donadio; J. Mitard; H. Dekkers; R. Delhougne; S. Subhechha; A. Chasin; M. J. Van Setten; L. Kljucar; M. Mao; H. Puliyalil; M. Pak; L. Teugels; D. Tsvetanova; K. Banerjee; L. Souriau; Z. Tokei; L. Goux; G. S. Kar</i>	
DOUBLE-GATE W-DOPED AMORPHOUS INDIUM OXIDE TRANSISTORS FOR MONOLITHIC 3D CAPACITORLESS GAIN CELL EDAM	613
<i>H. Ye; J. Gomez; W. Chakraborty; S. Spetalnick; S. Dutta; K. Ni; A. Raychowdhury; S. Datta</i>	
HIGHLY-STABLE (< 3% FLUCTUATION) AG-BASED THRESHOLD SWITCH WITH EXTREME-LOW OFF CURRENT OF 0.1 PA, EXTREME-HIGH SELECTIVITY OF 10⁹ AND HIGH ENDURANCE OF 10⁹ CYCLES	617
<i>Writam Banerjee; Ilya V. Karpov; Ashish Agrawal; Seonghun Kim; Seungwoo Lee; Sangmin Lee; Donghwa Lee; Hyunsang Hwang</i>	
MONOLITHIC 3D-IC BASED MASSIVELY PARALLEL COMPUTE-IN-MEMORY MACRO FOR ACCELERATING DATABASE AND MACHINE LEARNING PRIMITIVES	621
<i>Akshay Krishna Ramanathan; Srivatsa Srinivasa Rangachar; Je-Min Hung; Chun-Ying Lee; Cheng-Xin Xue; Sheng-Po Huang; Fu-Kuo Hsueh; Chang-Hong Shen; Jia-Min Shieh; Wen-Kuan Yeh; Mon-Shu Ho; Hariram Thirucherai Govindarajan; Jack Sampson; Meng-Fan Chang; Vij</i>	
A MACHINE-LEARNING-RESISTANT 3D PUF WITH 8-LAYER STACKING VERTICAL RRAM AND 0.014% BIT ERROR RATE USING IN-CELL STABILIZATION SCHEME FOR IOT SECURITY APPLICATIONS	625
<i>Jianguo Yang; Dengyun Lei; Deyang Chen; Jing Li; Haijun Jiang; Qingting Ding; Qing Luo; Xiaoyong Xue; Hangbing Lv; Xiaoyang Zeng; Ming Liu</i>	
OPPORTUNITIES AND LIMITATIONS OF EMERGING ANALOG IN-MEMORY COMPUTE DNN ARCHITECTURES	629
<i>Pouya Houshmand; Stefan Cosemans; Linyan Mei; Ioannis Papistas; Debjyoti Bhattacharjee; Peter Debacker; Arindam Mallik; Diederik Verkest; Marian Verhelst</i>	
ULTRA-LOW POWER FLEXIBLE PRECISION FEFET BASED ANALOG IN-MEMORY COMPUTING	633
<i>T. Soliman; F. Müller; T. Kirchner; T. Hoffmann; H. Ganem; E. Karimov; T. Ali; M. Lederer; C. Sudarshan; T. Kämpfe; A. Guntoro; N. Wehn</i>	
A SCALABLE DESIGN OF MULTI-BIT FERROELECTRIC CONTENT ADDRESSABLE MEMORY FOR DATA-CENTRIC COMPUTING	637
<i>Chao Li; Franz Müller; Tarek Ali; Ricardo Olivo; Mohsen Imani; Shan Deng; Cheng Zhuo; Thomas Kämpfe; Xunzhao Yin; Kai Ni</i>	
PRECISION OF SYNAPTIC WEIGHTS PROGRAMMED IN PHASE-CHANGE MEMORY DEVICES FOR DEEP LEARNING INFERENCE	641
<i>S. R. Nandakumar; Irem Boybat; Jin-Ping Han; Stefano Ambrogio; Praneet Adusumilli; Robert L. Bruce; Matthew Brightsky; Malte Rasch; Manuel Le Gallo; Abu Sebastian</i>	
3D RRAMS WITH GATE-ALL-AROUND STACKED NANOSHEET TRANSISTORS FOR IN-MEMORY-COMPUTING	645
<i>S. Barraud; M. Ezzadeen; D. Bosch; T. Dubreuil; N. Castellani; V. Meli; J. M. Hartmann; M. Mouhdach; B. Previtali; B. Giraud; J. P. Noël; G. Molas; J. M. Portal; E. Nowak; F. Andrieu</i>	
FULLY MEMRISTIVE SNNs WITH TEMPORAL CODING FOR FAST AND LOW-POWER EDGE COMPUTING	649
<i>Xumeng Zhang; Zuheng Wu; Jikai Lu; Jinsong Wei; Jian Lu; Jiaxue Zhu; Jie Qiu; Rui Wang; Kaihua Lou; Yongzhou Wang; Tuo Shi; Chunmeng Dou; Dashan Shang; Qi Liu; Ming Liu</i>	
CHALLENGES AND PERSPECTIVES IN THE MODELING OF SPIN QUBITS	653
<i>Y. M. Niquet; L. Hutin; B. Martinez Diaz; B. Venitucci; J. Li; V. Michal; G. Troncoso Fernández-Bada; H. Jacquinet; A. Amisse; A. Apra; R. Ezzouch; N. Piot; E. Vincent; C. Yu; S. Zihlmann; B. Brun-Barrière; V. Schmitt; E. Dumur; R. Maurand; X. Jehl; M. Sanquer; B. Bertrand; N. Rambal; H. Niebojewski; T. Bedecarrats; M. Casse; E. Catapano; P. A. Mortemousque; C. Thomas; Y. Thonnart; G. Billiot; A. Morel; J. Charbonnier; L. Pallegoix; D. Niegemann; B. Klemt; M. Urdampilleta; V. El Homsy; M. Nurizzo; E. Chanrion; B. Jadot; C. Spence; V. Thiney; B. Paz; S. de Franceschi, M. Vinet; T. Meunier</i>	
A SCALABLE ONE DIMENSIONAL SILICON QUBIT ARRAY WITH NANOMAGNETS	657
<i>G. Simion; F. A. Mohiyaddin; R. Li; M. Shehata; N. I. Dumoulin Stuyck; A. Elsayed; F. Ciobotaru; S. Kubicek; J. Jussot; B. T. Chan; Ts. Ivanov; C. Godfrin; A. Spessot; P. Matagne; B. Govoreanu; I. P. Radu</i>	
AB INITIO MODELING FRAMEWORK FOR MAJORANA TRANSPORT IN 2D MATERIALS: TOWARDS TOPOLOGICAL QUANTUM COMPUTING	661
<i>Y. Lee; T. Agarwal; M. Luisier</i>	
BENCHMARKING MONOLITHIC 3D INTEGRATION FOR COMPUTE-IN-MEMORY ACCELERATORS: OVERCOMING ADC BOTTLENECKS AND MAINTAINING SCALABILITY TO 7NM OR BEYOND	665
<i>Xiaochen Peng; Wriiddhi Chakraborty; Ankit Kaul; Wonbo Shim; Muhammad S. Bakir; Suman Datta; Shimeng Yu</i>	
RELIABILITY AND PERFORMANCE OF CMOS-COMPATIBLE MULTI-LEVEL GRAPHENE INTERCONNECTS INCORPORATING VIAS	669
<i>Kunjesh Agashiwala; Junkai Jiang; Chao-Hui Yeh; Kamyar Parto; Dujiao Zhang; Kaustav Banerjee</i>	

ATOMIC HYDROGEN EXPOSURE TO ENABLE HIGH-QUALITY LOW-TEMPERATURE SiO₂ WITH EXCELLENT PMOS NBTI RELIABILITY COMPATIBLE WITH 3D SEQUENTIAL TIER STACKING	673
<i>J. Franco; J.-F. De Marneffe; A. Vandooren; Y. Kimura; L. Nyns; Z. Wu; A.-M. El-Sayed; M. Jech; D. Waldhoer; D. Claes; H. Arimura; L.-A. Ragnarsson; V. Afanas'Ev; A. Stesmans; N. Horiguchi; D. Linten; T. Grasser; B. Kaczer</i>	
SUB-NS POLARIZATION SWITCHING IN 25NM FE FINFET TOWARD POST CPU AND SPATIAL-ENERGETIC MAPPING OF TRAPS FOR ENHANCED ENDURANCE	677
<i>Hagyoul Bae; Seung Geol Nam; Taehwan Moon; Yunseong Lee; Sanghyun Jo; Duk-Hyun Choe; Sangwook Kim; Kwang-Hee Lee; Jinseong Heo</i>	
HIGH-RADIATION HARDNESS 4H-SiC TRANSMITTANCE AMPLIFIER FEATURING STABLE OFFSET-VOLTAGE FOR ANALOG SENSORS IN NUCLEAR POWER PLANTS	681
<i>M. Masunaga; R. Kuwana; K. Egawa; H. Hayashi; T. Kawamura; I. Hara; D. Hisamoto; D. Ryuzaki</i>	
SECURE 3D CMOS CHIP STACKS WITH BACKSIDE BURIED METAL POWER DELIVERY NETWORKS FOR DISTRIBUTED DECOUPLING CAPACITANCE	685
<i>Hiroki Sonoda; Kazuki Monta; Takaaki Okidono; Yuuki Araga; Naoya Watanabe; Haruo Shimamoto; Katsuya Kikuchi; Noriyuki Miura; Takuji Miki; Makoto Nagata</i>	
A NOVEL COMPLEMENTARY ARCHITECTURE OF ONE-TIME-PROGRAMMABLE MEMORY AND ITS APPLICATIONS AS PHYSICAL UNCLONABLE FUNCTION (PUF) AND ONE-TIME PASSWORD	689
<i>W. C. Wang; C. C. Chuang; C. W. Chang; E. R. Hsieh; H. W. Chen; Steve S. Chung</i>	
THE OVERVIEW OF CURRENT INTERCONNECT TECHNOLOGY CHALLENGES AND FUTURE OPPORTUNITIES	693
<i>M. H. Lee; Winston S. Shue</i>	
INFLECTION POINTS IN INTERCONNECT RESEARCH AND TRENDS FOR 2NM AND BEYOND IN ORDER TO SOLVE THE RC BOTTLENECK	697
<i>Z. Tokci; V. Vega; G. Murdoch; M. O'Toole; K. Croes; R. Baert; M. Van Der Veen; C. Adelman; J. P. Soulié; J. Boemmels; C. Wilson; S. H. Park; K. Sankaran; G. Pourtois; J. Sweerts; S. Paolillo; S. Decoster; M. Mao; F. Lazzarino; J. Versluijs; V. Blanco;</i>	
NARROW INTERCONNECTS: THE MOST CONDUCTIVE METALS	701
<i>Daniel Gall; Atharv Jog; Tianji Zhou</i>	
TOPOLOGICAL SEMIMETALS FOR SCALED BACK-END-OF-LINE INTERCONNECT BEYOND CU	705
<i>Ching-Tzu Chen; Utkarsh Bajpai; Nicholas A. Lanzillo; Chuang-Han Hsu; Hsin Lin; Gengchiao Liang</i>	
STAGGERED METALLIZATION WITH AIR GAPS FOR INDEPENDENTLY TUNED INTERCONNECT RESISTANCE AND CAPACITANCE	709
<i>Kevin L. Lin; Mark Anders; Robert Bristol; Michael Christenson; Giselle Elbaz; Brandon Holybee; Himanshu Kaul; Mauro Kobrinsky; Ram Krishnamurthy; Miriam Reshotko; Hui Jae Yoo</i>	
FROM INTERCONNECT MATERIALS AND PROCESSES TO CHIP LEVEL PERFORMANCE: MODELING AND DESIGN FOR CONVENTIONAL AND EXPLORATORY CONCEPTS	713
<i>V. Huang; D. Shim; H. Simka; A. Naeemi</i>	
SILICON COMPATIBLE OPTICAL INTERCONNECT AND MONOLITHIC 3-D INTEGRATION	717
<i>Krishna C. Saraswat</i>	
LOW POWER CONSUMPTION AND HIGH RESOLUTION 1280X960 GATE ASSISTED PHOTONIC DEMODULATOR PIXEL FOR INDIRECT TIME OF FLIGHT	721
<i>Y. Ebiko; H. Yamagishi; K. Tatani; H. Iwamoto; Y. Moriyama; Y. Hagiwara; S. Maeda; T. Murase; T. Suwa; H. Arai; Y. Isogai; S. Hida; S. Kameda; T. Terada; K. Koiso; F. T. Brady; S. Han; A. Basavalingappa; T. Michiel; T. Ueno</i>	
A 2.8 μM PIXEL FOR TIME OF FLIGHT CMOS IMAGE SENSOR WITH 20 KE-FULL-WELL CAPACITY IN A TAP AND 36 % QUANTUM EFFICIENCY AT 940 NM WAVELENGTH	725
<i>Yonghun Kwon; Sungyoung Seo; Sunghyuck Cho; Sung-Ho Choi; Taeun Hwang; Youngchan Kim; Young-Gu Jin; Youngsun Oh; Min-Sun Keel; Daeyun Kim; Myunghan Bae; Yeomyung Kim; Seung-Chul Shin; Sunju Hong; Seok-Ha Lee; Ho Woo Park; Yitae Kim; Kyoungmin Koh; Jungchak</i>	
FUNDAMENTAL CHALLENGES IN AUGMENTED REALITY DISPLAY TECHNOLOGY	729
<i>M. Colburn</i>	
ENHANCED LIGHT OUTCOUPLING FROM OLEDs BY SUPPRESSING GUIDED MODES FORMATION USING AN ULTRATHIN FLEXIBLE TRANSPARENT CONDUCTOR	733
<i>Changyeong Jeong; Yong-Bum Park; L. Jay Guo</i>	
LOW VOLTAGE, HIGH BRIGHTNESS CMOS LEDS	737
<i>J. Xue; J. Kim; A. Mestre; K. M. Tan; D. Chong; S. Roy; H. Nong; K. Y. Lim; D. Gray; D. Kramnik; A. Atabaki; E. Quek; R. J. Ram</i>	
GIGAHERTZ LARGE-AREA-ELECTRONICS RF SWITCH AND ITS APPLICATION TO RECONFIGURABLE ANTENNAS	741
<i>Can Wu; Yue Ma; Suresh Venkatesh; Yoni Mehlman; Sigurd Wagner; James C. Sturm; Naveen Verma</i>	
MILLIMETER-WAVE MULTI-ANTENNA/MIMO TECHNIQUES FOR 5G NR BASE-STATIONS	745
<i>Rui Hou; Bo Göransson</i>	
A DEEP LEARNING ENABLED UNIVERSAL DPD SYSTEM	749
<i>I. Chih-Lin; Yingchao Lin; Guizhen Wang</i>	
MILLIMETER-WAVE CMOS PHASED-ARRAY TRANSCIEVER FOR 5G AND BEYOND	753
<i>Kenichi Okada</i>	
PD-SOI CMOS AND SIGE BICMOS TECHNOLOGIES FOR 5G AND 6G COMMUNICATIONS	757
<i>P. Chevalier; F. Giansello; A. Pallotta; J. Azevedo Goncalves; G. Bertrand; J. Borrel; L. Boissonnet; E. Brezza; M. Buczko; E. Canderle; D. Celi; S. Cremer; N. Derrier; C. Diouf; C. Durand; F. Foussadier; P. Garcia; N. Guitard; A. Fleury; A. Gauthier; O.</i>	
HETEROGENEOUS INTEGRATION FOR HIGH FREQUENCY RF APPLICATIONS	761
<i>A. Gutierrez-Aitken</i>	
INNOVATIVE SMART CUT™ PIEZO ON INSULATOR (POI) SUBSTRATES FOR 5G ACOUSTIC FILTERS	765
<i>E. Butaud; S. Ballandras; M. Bousquet; A. Drouin; B. Tavel; I. Huyet; A. Clairet; I. Bertrand; A. Ghorbel; A. Reinhardt</i>	

CHEMICAL SENSING IN AQUEOUS MEDIA BY ORGANIC TFTS	769
<i>T. Minami</i>	
EXTENDED-GATE FET CORTISOL SENSOR FOR STRESS DISORDERS BASED ON APTAMERS-DECORATED GRAPHENE ELECTRODE: FABRICATION, EXPERIMENTS AND UNIFIED ANALOG PREDICTIVE MODELING	773
<i>L. Capua; S. Sheibani; S. Kamaei; J. Zhang; A. M. Ionescu</i>	
EFFICIENT IMPROVEMENT OF SENSING PERFORMANCE USING CHARGE STORAGE ENGINEERING IN LOW NOISE FET-TYPE GAS SENSORS	777
<i>Wonjun Shin; Seongbin Hong; Yujeong Jeong; Gyuweon Jung; Jinwoo Park; Dongseok Kwon; Dongkyu Jang; Donghee Kim; Byung-Gook Park; Jong-Ho Lee</i>	
50 NM GATE LENGTH FINFET BIOSENSOR & THE OUTLOOK FOR SINGLE-MOLECULE DETECTION	781
<i>S. Santermans; D. Barge; G. Hellings; C. B. Mori; K. J. Migacz; J. Rip; V. Spampinato; R. Vos; B. Du Bois; A. R. Chaudhuri; J. A. Martino; M. Heyns; S. Severi; W. Van Roy; K. Martens</i>	
LARGE-AREA MANUFACTURABLE ACTIVE MATRIX DIGITAL MICROFLUIDICS PLATFORM FOR HIGH-THROUGHPUT BIOSAMPLE HANDLING	785
<i>H. Ma; S. Shi; K. Jin; D. Wang; S. Hu; Y. Su; Y. Zhang; J. Li; Z. Liu; C. Jiang; L. Feng; X. Guo; A. Nathan</i>	
IN-MEMORY-SEARCHING ARCHITECTURE BASED ON 3D-NAND TECHNOLOGY WITH ULTRA-HIGH PARALLELISM	789
<i>Po-Hao Tseng; Feng-Ming Lee; Yu-Hsuan Lin; Liang-Yu Chen; Yung-Chun Li; Han-Wen Hu; Yun-Yuan Wang; Chih-Chang Hsieh; Ming-Hsiu Lee; Hsiang-Lan Lung; Kuang-Yeu Hsieh; Keh-Chung Wang; Chih-Yuan Lu</i>	
UNASSISTED TRUE ANALOG NEURAL NETWORK TRAINING CHIP	793
<i>Y. Kohda; Y. Li; K. Hosokawa; S. Kim; R. Khaddam-Aljameh; Z. Ren; P. Solomon; T. Gokmen; S. Rajalingam; C. Baks; W. Haensch; E. Leobandung</i>	
ACCELERATED LOCAL TRAINING OF CNNs BY OPTIMIZED DIRECT FEEDBACK ALIGNMENT BASED ON STOCHASTICITY OF 4 MB C-DOPED $Ge_2Sb_2Te_5$ PCM CHIP IN 40 NM NODE	797
<i>Yingming Lu; Xi Li; Longhao Yan; Teng Zhang; Yuchao Yang; Zhitang Song; Ru Huang</i>	
MONOLITHIC 3D INTEGRATION OF HIGH ENDURANCE MULTI-BIT FERROELECTRIC FET FOR ACCELERATING COMPUTE-IN-MEMORY	801
<i>S. Dutta; H. Ye; W. Chakraborty; Y.-C. Luo; M. San Jose; B. Grisafe; A. Khanna; I. Lightcap; S. Shinde; S. Yu; S. Datta</i>	
HIGH-DENSITY 3D MONOLITHICALLY INTEGRATED MULTIPLE 1T1R MULTI-LEVEL-CELL FOR NEURAL NETWORKS	805
<i>E. Esmanhotto; L. Brunet; N. Castellani; D. Bonnet; T. Dalgaty; L. Grenouillet; D. R. B. Ly; C. Cagli; C. Vizioz; N. Allouti; F. Laulagnet; O. Gully; N. Bernard-Henriques; M. Bocquet; G. Molas; P. Vivet; D. Querlioz; J. Portal; S. Mitra; F. Andrieu; C. Fenouillet-Beranger; E. Nowak; E. Vianello</i>	
ANALOG ERROR CORRECTING CODES FOR DEFECT TOLERANT MATRIX MULTIPLICATION IN CROSSBARS	809
<i>Can Li; Ron M. Roth; Cat Graves; Xia Sheng; John Paul Strachan</i>	
HIGH POWER GRAPHENE MICRO-SUPERCAPACITORS	817
<i>R. B. Kaner; C. Wang; M. El-Kady; V. Strauss; A. Borenstein; M. Muni; H. Huang; X. Chang; S. Qu; K. Sung</i>	
MEMS VIBRATIONAL ENERGY HARVESTER FOR IOT WIRELESS SENSORS	821
<i>H. Toshiyoshi</i>	
HIGH-VOLTAGE MICRO-PLASMA SWITCH FOR EFFICIENT POWER MANAGEMENT OF TRIBOELECTRIC KINETIC ENERGY HARVESTERS	825
<i>P. Bassat; H. Zhang; F. Marty; A. Delbani; N. Hodzic; A. Karami; D. Galayko</i>	
RADIATIVE WIRELESS POWER TRANSMISSION: FROM INDOOR TO IN-BODY APPLICATIONS	829
<i>Hubregt J. Visser</i>	
WIRELESS POWER TRANSFER FOR INTERNET OF THINGS	833
<i>Y. Kawahara; T. Sasatani</i>	
MM-WAVE BACKSCATTER FRONT-END FOR 5G-IOT/WPT APPLICATIONS	837
<i>D. Matos; R. Correia; N. B. Carvalho</i>	
THE WONDERFUL WORLD OF DESIGNER GE QUANTUM DOTS	841
<i>I-Hsiang Wang; Po-Yu Hong; Kang-Ping Peng; Horng-Chih Lin; Thomas George; Pei-Wen Li</i>	
COUPLER CHARACTERIZATION OF SUPERCONDUCTING TRANSMONS QUBITS FOR CROSS-RESONANCE GATE	845
<i>Hanhee Paik; Srikanth Srinivasan; Sami Rosenblatt; José Chavez-Garcia; Daniela Bogorin; Oblesh Jinka; George Keefe; Dongbing Shao; Jeng-Bang Yau; Markus Brink; Jerry M. Chow</i>	
A FLEXIBLE 300 MM INTEGRATED SI MOS PLATFORM FOR ELECTRON- AND HOLE-SPIN QUBITS EXPLORATION	849
<i>R. Li; N. I. Dumoulin Stuyck; S. Kubicek; J. Jussot; B. T. Chan; F. A. Mohiyaddin; A. Elsayed; M. Shehata; G. Simion; C. Godfrin; Y. Canvel; Ts. Ivanov; L. Goux; B. Govoreanu; I. P. Radu</i>	
DISPERSIVE VS CHARGE-SENSING READOUT FOR LINEAR QUANTUM REGISTERS	853
<i>A. Aprà; A. Crippa; M. L. V. Tagliaferri; J. Li; R. Ezzouch; B. Bertrand; L. Hutin; N. Rambal; E. Catapano; H. Niebojewsky; T. Bedecarrats; M. Vinet; M. Urdampilleta; T. Meunier; Y. M. Niquet; E. Dumur; M. Sanquer; X. Jehl; R. Maurand; S. De Franceschi</i>	
CRYOGENIC BENCHMARKS OF EMBEDDED MEMORY TECHNOLOGIES FOR RECURRENT NEURAL NETWORK BASED QUANTUM ERROR CORRECTION	857
<i>Panni Wang; Xiaochen Peng; Wriddhi Chakraborty; Asif Islam Khan; Suman Datta; Shimeng Yu</i>	
A HIGH-PERFORMANCE AND CALIBRATION-FREE TRUE RANDOM NUMBER GENERATOR BASED ON THE RESISTANCE PERTURBATION IN RRAM ARRAY	861
<i>Bohan Lin; Bin Gao; Yachuan Pang; Wenqiang Zhang; Jianshi Tang; He Qian; Huaqiang Wu</i>	
MACHINE LEARNING FOR CIRCUIT AGING SIMULATION	865
<i>E. Rosenbaum; J. Xiong; A. Yang; Z. Chen; M. Raginsky</i>	

A NOVEL PUF USING STOCHASTIC SHORT-TERM MEMORY TIME OF OXIDE-BASED RRAM FOR EMBEDDED APPLICATIONS	869
<i>Jianguo Yang; Deyang Chen; Qinting Ding; Jinbei Fang; Xiaoyong Xue; Hangbing Lv; Xiaoyang Zeng; Ming Liu</i>	
NOVEL CONCEPT OF HARDWARE SECURITY IN USING GATE-SWITCHING FINFET NONVOLATILE MEMORY TO IMPLEMENT TRUE-RANDOM-NUMBER GENERATOR	873
<i>W. Y. Yang; B. Y. Chen; C. C. Chuang; E. R. Hsieh; K. S. Li; Steve S. Chung</i>	
HYDROGEN ABSORPTION METHOD USING HFOX IN CRYSTALLINE IN-GA-ZN OXIDE FETS FOR NVM APPLICATIONS	877
<i>T. Ono; Y. Yanagisawa; Y. Komatsu; T. Aoki; Y. Jimbo; S. Ito; Y. Yamane; N. Okuno; H. Kunitake; H. Komagata; S. Sasagawa; S. Yamazaki</i>	
INTERPLAY OF SWITCHING CHARACTERISTICS, CYCLING ENDURANCE AND MULTILEVEL RETENTION OF FERROELECTRIC CAPACITOR	881
<i>Jae Hur; Panni Wang; Zheng Wang; Gihun Choe; Nujhat Tasneem; Asif Islam Khan; Shimeng Yu</i>	
DEEP INSIGHTS INTO THE FAILURE MECHANISMS IN FIELD-CYCLED FERROELECTRIC $\text{HF}_{0.5}\text{ZR}_{0.5}\text{O}_2$ THIN FILM: TDD CHARACTERIZATIONS AND FIRST-PRINCIPLES CALCULATIONS	885
<i>Wei Wei; Weiqiang Zhang; Fei Wang; Xiaolei Ma; Qianwen Wang; Pengpeng Sang; Xuepeng Zhan; Yuan Li; Lu Tai; Qing Luo; Hangbing Lv; Jiezhi Chen</i>	
A SELECTIVELY COLORFUL YET CHILLY PERSPECTIVE ON THE HIGHS AND LOWS OF DIELECTRIC MATERIALS FOR CMOS NANOELECTRONICS	889
<i>S. King; J. Plombon; J. Bielefeld; J. Blackwell; S. Vyas; R. Chebiam; C. Naylor; D. Michalak; M. Kobrinsky; F. Gstrein; M. Metz; J. Clarke; R. Thapa; M. Paquette; V. Vemuri; N. Strandwitz; Y. Fan; M. Orłowski</i>	
WAFER-SCALE INTEGRATION OF DOUBLE GATED WS_2-TRANSISTORS IN 300MM SI CMOS FAB	893
<i>I. Asselberghs; Q. Smets; T. Schram; B. Groven; D. Verreck; A. Afzalian; G. Arutchevian; A. Gaur; D. Cott; T. Maurice; S. Brems; K. Kennes; A. Phommahaxay; E. Dupuy; D. Radisic; J.-F. De Marneffe; A. Thiam; W. Li; K. Devriendt; C. Huyghebaert; D. Lin; M. Ca</i>	
SWITCHABLE NAND AND NOR LOGIC COMPUTING IN SINGLE TRIPLE-GATE MONOLAYER MOS_2 N-FET	897
<i>Yun-Yan Chung; Chao-Ching Cheng; Bo-Kai Kang; Wei-Chen Chueh; Shih-Yun Wang; Chen-Han Chou; Terry Y. T. Hung; Shin-Yuan Wang; Wen-Hao Chang; Lain-Jong Li; Chao-Hsin Chien</i>	
FIRST DEMONSTRATION OF ULTRAFAST LASER ANNEALED MONOLITHIC 3D GATE-ALL-AROUND CMOS LOGIC AND FET MEMORY WITH NEAR-MEMORY-COMPUTING MACRO	901
<i>Fu-Kuo Hsueh; Je-Min Hung; Sheng-Po Huang; Yen-Hsiang Huang; Cheng-Xin Xue; Chang-Hong Shen; Jia-Min Shieh; Wen-Cheng Chiu; Chao-Cheng Lin; Bo-Yuan Chen; Szu-Ching Liu; Shih-Wei Chen; Deng-Yan Niou; Wen-Hsien Huang; Kai-Shin Li; Kun-Kin Lin; Da-Chiang Cha</i>	
10-NM CHANNEL LENGTH INDIUM-TIN-OXIDE TRANSISTORS WITH $I_{\text{ON}} = 1860 \mu\text{A}/\mu\text{M}$, $G_{\text{M}} = 1050 \mu\text{S}/\mu\text{M}$ AT $V_{\text{DS}} = 1 \text{ V}$ WITH BEOL COMPATIBILITY	905
<i>Shengman Li; Chengru Gu; Xuefei Li; Ru Huang; Yanqing Wu</i>	
CRYSTAL-ORIENTATIONAL-TOLERANT VOLTAGE REGULATOR USING MONOLITHIC 3D BEOL FINFETS IN SINGLE-CRYSTAL ISLANDS FOR ON-CHIP POWER DELIVERY NETWORK	909
<i>Po-Tsang Huang; Yu-Wei Liu; Kuan-Fu Lai; Yun-Ping Lan; Tzung-Han Tsai; Bo-Jheng Shih; Ping-Yi Hsieh; Chih-Chao Yang; Chang-Hong Shen; Jia-Min Shieh; Da-Chiang Chang; Kuan-Neng Chen; Wen-Kuan Yeh; Chenming Hu</i>	
DTCO LAUNCHES MOORE'S LAW OVER THE FEATURE SCALING WALL	913
<i>V. Moroz; X.-W. Lin; P. Asenov; D. Sherlekar; M. Choi; L. Sponton; L. S. Melvin; J. Lee; B. Cheng; A. Nannipieri; J. Huang; S. Jones</i>	
ADVANCED NODE DTCO IN THE EUV ERA	917
<i>A. Wei; C. Wallace; M. Phillips; J. Knudsen; S. Chakravarty; M. Shamanna; R. Brain</i>	
NEXT-GENERATION DESIGN AND TECHNOLOGY CO-OPTIMIZATION (DTCO) OF SYSTEM ON INTEGRATED CHIP (SOIC) FOR MOBILE AND HPC APPLICATIONS	921
<i>Y.-K. Cheng; F. Lee; M.-F. Chen; J. Yuan; T.-C. Huang; K.-J. Chen; C.-T. Wang; C.-L. Chen; C.-H. Tsai; Douglas Yu</i>	
DTCO INCLUDING SUSTAINABILITY: POWER-PERFORMANCE-AREA-COST-ENVIRONMENTAL SCORE (PPACE) ANALYSIS FOR LOGIC TECHNOLOGIES	925
<i>M. Garcia Bardon; P. Wuytens; L.-A. Ragnarsson; G. Mirabelli; D. Jang; G. Willems; A. Mallik; A. Spessot; J. Ryckaert; B. Parvais</i>	
ENABLING EFFICIENT DESIGN-TECHNOLOGY INTERACTION BY SPEC-DRIVEN EXTRACTION FLOW	929
<i>Huan-Lin Chang; Yutao Ma; Zhihong Liu</i>	
MRAM DTCO AND COMPACT MODELS	933
<i>Jeehwan Song; Jian-Ping Wang; Chris H. Kim</i>	
ENABLING DESIGN TECHNOLOGY CO-OPTIMIZATION OF SRAMS THROUGH OPEN-SOURCE SOFTWARE	937
<i>Matthew Guthaus; Hunter Nichols; Jesse Cirimelli-Low; Joseph Kunzler; Bin Wu</i>	
Author Index	